

Search for the Fractional Josephson Effect in Topological and Nontopological Materials

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May 2024 Christian Schönenberger Quantum- and Nanoelectronics group <u>www.nanoelectronics.ch</u>

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Team(s) and Funding

Roy Haller





Jann Ungerer

Libin Wang Carlo Ciaccia



InAs nanowires: Jesper Nygard et al. University of Copenhagen, Denmark

InAs heterostructure growth:

Mike Manfra's group Purdue University and Microsoft Quantum@ Purdue

WTe₂ growth: David Mandrus' group Materials Science and Engineering, The University of Tennessee

Cd3As2

Minkyung Jung et al. DGIST, Daegu Gyeongbuk, Institute of Scienc & technology, Korea



Artem Kononov Martin Endres Fabian Opliger

HgTe device: provided by Dieter Weiss' **Group** University of Regensburg,

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QUANTERA

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Introduction to the Fractional Josephson Effect

A Short Introduction to Topological Superconductors

--- A Glimpse of Topological Phases of Matter

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Dec. 09, 2015 @ Superconductivity Course, ETH jyong-hao.chen@psi.ch

Quantum Hall Effect: chiral gapless edge states Halperin, 1982

Chiral edge state (skipping orbit picture)



Gapless excitations at the edges

- Quantum Hall state is a topological insulator (TI), where the bulk is gapped due to Landau quantization.
- Typical for TI's are compressible (conducting) edge modes (in this case, chiral modes). This is also known under the term "bulk-boundary correspondence"
- If time-reversal symmetry is maintained, there are further classes of TI, e.g. the **Quantum Spin Hall insulator**

2005: Quantum Spin Hall Effect/Z₂ topological insulator



Experimental observation of HgTe TI

Theoretically predicted in 2006





Bernevig, Hughes, and Zhang, Science, 2006



- Experimentally found in Nov. 2007 Konig et al., Science, 2007
- Measure conductance while tuning E_F through the bulk energy gap
- edge state conductance 2e²/h observed independent of W and L





I. d=5.5nm (normal) Insulating in gap II-IV d=7.3nm (inverted) conducting in gap II. L = 20 μ m (> L_{in}) III. L = 1 μ m W = 1 μ m

IV. L = 1 μm W = .5 μm

Quantum Spin Hall insulator maintain Tsymmetry leading to helical edge states

Introduction to the Fractional Josephson Effect

New topological phases of matter



Introduction to the Fractional Josephson Effect

Superconducting proximity effect

Minimal surface state model:

 $H_{0} = \psi^{\dagger} (-iv\vec{\sigma} \ \vec{\nabla} - \mu)\psi$ $V_{S} = \Delta \psi^{\dagger}_{\uparrow} \psi^{\dagger}_{\downarrow} + \Delta^{*} \psi_{\downarrow} \psi_{\uparrow}$ s wave su



φ = π φ ≠ π

q



• 1D helical Majorana edge states at SC-TI-SC Josephson junction



$$H = -i\hbar \mathsf{V}_{\mathsf{F}} \left(\gamma_L \partial_x \gamma_L - \gamma_R \partial_x \gamma_R \right) + i\Delta \cos(\phi/2) \gamma_L \gamma_R$$

• 1D chiral Majorana edge states at superconductor-magnet interfaces





a device similar to Mourik et al. 2012 that started the "race" for Majorana fermions in 1d, topological qubits, and ...

What I will be focusing on

- We will discuss the physics (mostly experimental) of Josephson junctions (JJ) realized with supposedly topological materials
- The **fractional Josephson effect** could be a hint for the presence of MBS, and hence, topological superconductivity



Introduction (Josephson relations)



Introduction to the Fractional Josephson Effect

Introduction (Josephson relations)



Introduction (Devices)



Introduction (Andreev level)

atomic contact = prototype single channel Josephson junction in the short-junction limit to demonstrate **Andreev Bound State(s)** (ABS)



for example:

M. F. Goffman et al. Supercurrent in atomic point contacts and Andreev states, Phys. Rev. Lett. 85, 170 (2000).

L. Bretheau et al. Exciting Andreev pairs in a superconducting atomic contact, Nature 499 (7458), 312-315 (2013).

formation of Andreev Bound State



 $I(\varphi) = \frac{2e}{\hbar} \frac{\partial E(\varphi)}{\partial \varphi}$

Α

E

Δ

 $E_A(\delta)$

 $-E_A(\delta)$

 $-\Delta$



Introduction to the Fractional Josephson Effect







if parity is conserved, the CPR (current-phase relation) has a **doubled** periodicity of 4π instead of 2π

if parity is not conserved, the 2π periodicity of the CPR is restored



if parity is conserved, the CPR (current-phase relation) has a **doubled** periodicity of 4π instead of 2π

if parity is not conserved, the 2π -periodicity of the CPR is restored



if phase evolution in a **dynamic process** is faster than the "poisoning" time, one expects to still see a contribution from the 4π -periodicity

but note, a trivial CPR can also assume a 4π -periodic contribution through Landau-Zener transitions

The idea is to **do "proper" dynamic** experiments in the search of a "higherorder" periodicity, also termed the "fractional" Josephson effect.

How to access the CPR in experiments

- 1. measure the **AC Josephson effect** while voltage biasing the junction
 - a) measure the emitted microwave radiation
 - b) explore the I-V characteristics while exposing the junction to an external microwave field → Shapiro steps
- 2. measure the **inductance of the junction** (susceptibility) as a function of flux bias
- 3. use an **asymmetric DC-SQUID** to measure the CPR

Asymmetric SQUID / RF-SQUID

asymmetric DC SQUID



RF-SQUID with "qubit" readout



see for the concept: R. Haller et al. *Phase-dependent microwave response* of a graphene Josephson junction, Phys. Rev. Research **4**, 013198 (2022)

Introduction to the Fractional Josephson Effect



here: half-shell InAs NWs from UCPH (J. Nygard et al.)

RF-SQUID with "qubit" readout



Superconducting loop

- Sputtered NbTiN (120 nm)
- Loop 100 um x 30 um (1 uT)
 - PMMA/MA (large undercut)
- Ar-plasma
- MBE-grown wurtzite InAs NW with epitaxial aluminum half shell
 - NW deposition with micromanipulator
 - Partially remove shell with wet etching process (MF321)
- Phase biasing via flux line
- Tuning transparency via gate
 - Ground reference needed
 - Side gate 900 nm apart

Introduction to the AC Josephson Effect in the Experiment, i.e. a) Josephson radiation b) Shapiro steps

Introduction (how to drive the JJ)



"truly" DC voltage biased \rightarrow ideal AC Josephson effect (not useful, need a "receiver")



"truly" DC current biased \rightarrow used to determine the critical current





current-biased V(I) curves

Introduction (how to drive the JJ)



"truly" DC voltage biased \rightarrow ideal AC Josephson effect (not useful, need a "receiver")



"truly" DC current biased \rightarrow used to determine the critical current







 V_{DC}

DC-bias

Introduction (how to drive the JJ)





$$R_s C \frac{\hbar}{2e} \frac{\partial^2 \varphi}{\partial t^2} + I_c R_s \sin(\varphi) + \frac{\hbar}{2e} \frac{\partial \varphi}{\partial t} = V_{DC}$$

in the "frictional-sliding" limit, one obtains as condition for an approximate $\varphi \doteq \omega t \approx \frac{2e}{\hbar} V_{DC} t$

 $1/\tau_{RC} \gg \omega \gg RI_c \left(\frac{2e}{\hbar}\right)$

In "general" we know that the CPR can be written as a Fourier series:

$$I_s(\varphi) = \sum_k (-1)^{k-1} A_k \sin(k\varphi),$$

An example is a junction with highly transmissive channels. Current-Phase Relation:



Assume, we could **perfectly DC bias** the junction with **voltage** *V*. The **phase** would then evolve with a constant velocity. The **Fourier spectrum** of the AC current contains harmonics at frequencies that are integer multiples of the fundamental Josephson frequency $f_I = 2eV/h$:

$$I_s(t) = \sum_{k=1}^{k-1} (-1)^{k-1} A_k \sin\left(k\frac{2eV}{\hbar}t\right)$$

If the junctions emits AC radiation, the **power spectral density** of the harmonics with index k would correspond to $|A_k|^2$

AC Josephson Effect with higher harmoni

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A different (more QM-like) description: inelastic tunneling of Cooper-pairs (charge 2e)



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A different (more QM-like) description: inelastic tunneling of Cooper-pairs (charge 2e) / h/e



AC Josephson (relevance for metrology

$$\frac{f_{\rm J}}{V} = \frac{2e}{h} = \Phi_0^{-1} = 483.6 \,\rm MHz \, \mu V^{-1}$$

AC Quantum Voltmeter Cooler

Programmable Josephson Voltage Standard



DESCRIPTION

The **cryocooled AC Quantum Voltmeter** is a turn-key programmable Josephson voltage standard system applicable for the highest level of precision voltage measurements from DC up to kHz frequencies. It was developed by Supracon in cooperation with the Physikalisch-Technische Bundesanstalt Braunschweig (PTB) and esz AG. It facilitates a variety of voltage calibrations and measuring functions:

- Primary DC & AC Josephson voltage standard up to kHz frequencies,
- Calibration of calibrators,
- Calibration of secondary voltage standards,
- Calibration of voltmeter linearity,
- Calibration of thermal converters (optional),
- Voltage source with ultimate precision and lowest noise level

The cryocooled **AC Quantum Voltmeter** consists of the following components:

- 1. 10 V programmable JVS array on thermal interface
- 2. Two-stage Pulse Tube Cooler
- 3. Air-cooled Compressor, 4 kW input power
- 4. Compact 70 GHz microwave source
- 5. Programmable 20 channel bias source
- 6. Control electronics with optical isolation unit
- 7. Nanovoltmeter as DC null detector
- Sampler for AC voltage measurements
 Waveform generator with synchronisation unit
- 10. Multiplexer with polarity switch
- 11. Host computer with control software
- 12. Sensors for temperature, humidity, and pressure
- 13. Optional: Vacuum pump.
 - GPS 10 MHz frequency reference



AC Josephson Effect in Devices Fabricated using Topological and Nontopological materials

- a) we can try to DC bias a JJ and stud the emission spectrum
- b) but we could also **radiate onto the JJ** with a fixed external Rf source at a drive frequency $f_D \rightarrow$ Shapiro steps (spikes) in the I-V characteristics at voltage values corresponding to $V = hf_D/2e$.





 $\ddot{\varphi} + \frac{1}{RC} \dot{\varphi} + \omega_p^2 \sin(\varphi) = \frac{I}{I_c} \omega_p^2$ $\omega_p = \sqrt{2eI_c/\hbar C} \qquad \text{Plasmafrequency}$ $Q = RC\omega_p \qquad \text{quality factor}$

$$U(\phi) = -E_J \cos(\phi) - rac{\hbar I_{tot}}{2e} \phi \hspace{0.5cm} egin{array}{c} E_J = rac{I_c \cdot \hbar}{2e} \ I_{ ext{tot}} = I_{ ext{DC}} + I_{ ext{rf}} \end{array}$$

Mechanical analog: phase particle moving in potential U





Let us add in addition an **AC source** driving at frequency f_d .

Due to the non-linearity of the Josephson circuit, the internal Josephson AC signal and the external can mix. This gives rise to **current spikes** (underdamped) or **Shapiro voltage steps** (overdamped and current biased JJ)



 $\ddot{\varphi} + \frac{1}{RC} \dot{\varphi} + \omega_p^2 \sin(\varphi) = \frac{I}{I_c} \omega_p^2$ $\omega_p = \sqrt{2eI_c/\hbar C} \qquad \text{Plasmafrequency}$ $Q = RC\omega_p \qquad \text{quality factor}$

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- I _c

0

l_{dc}

...the easiest way to see this is in the case of an applied AC voltage source:

AC voltage bias:
$$V(t) = V_{DC} + V_{rf} \cos(\omega t)$$

 $I(t) = I_c \cdot \sin[\frac{2e}{\hbar}V_{DC}t + \frac{2e}{\hbar}\frac{V_{rf}}{\omega} \cdot \sin(\omega t) + \phi_0]$
 $I(t) = I_c \cdot \sum_{n=-\infty}^{+\infty} (-1)^n J_n(\frac{2eV_{rf}}{\hbar\omega}) \sin[(\omega_{DC} - n\omega)t + \phi_0] + V_{DC}/R$
here $\omega_{DC} = \omega_J = 2eV_{DC}/\hbar$
it is a synchronization
effect taking place
between the external
drive and the AC
Josephson
effect. It relies on the
non-linearity (mixing)

for step *n* the phase advances by $n2\pi$ per period of the drive leading to $V_n = \frac{\hbar}{2e} n\omega$

2π

π x

l_c

 $I_{\rm DC} + I_{\rm rf}/$

 $I_{\rm rf}$





E. Bocquillon et al., Nature Nanotechnology 12, 137 (2016)

Selection of published Results

Info doe the tar evise fasting topological and Nontopological materials

The fractional a.c. Josephson effect in a semiconductor-superconductor nanowire as a signature of Majorana particles



Nature Phys. 8, 795 (2012)



ARTICLE

Received 15 Sep 2015 | Accepted 27 Nov 2015 | Published 21 Jan 2016

OPEN DOI: 10.1038/ncomms10303

4π -periodic Josephson supercurrent in HgTe-based topological Josephson junctions

J. Wiedenmann^{1,*}, E. Bocquillon^{1,*}, R.S. Deacon^{2,3,*}, S. Hartinger¹, O. Herrmann¹, T.M. Klapwijk^{4,5}, L. Maier¹, Shapiro steps C. Ames¹, C. Brüne¹, C. Gould¹, A. Oiwa⁶, K. Ishibashi^{2,3}, S. Tarucha^{3,7}, H. Buhmann¹ & L.W. Molenkamp¹ b b а ε(φ) Nb 6 :2.7 GHz Λ f=5.3 GHz HgTe dc voltage V (hf/2e) 4 f=11.2 GHz 1–4 u С 2 f=11.2 GHz f=2.7 GHz 6 6 0 dc voltage V (hf/2e) CdTe Δ -2 2 2 -4 0 0 -3 -2 -1 0 2 3 -2 1 dc current / (µA) -4 missing first odd Shapiro step -6 ,00 00,00,00 0 Bin counts (nA)

а

nature nanotechnology

Gapless Andree Hall insulator H

Erwann Bocquillon^{1*†}, Russell S. Teunis M. Klapwijk⁴, Christoph E and Laurens W. Molenkamp¹

In recent years, Majorana physics has at fault-tolerant topological quantum comp and electronic properties in a topological experimental evidence for topological s exhibits the quantum spin Hall (QSH) eff in the superconducting phase difference, this response like that of a supercondu 4π -periodic supercurrent originates fron the QSH regime, and thus provide evider



Article

Induced Topological Superconductivity in a BiSbTeSe₂-Based Josephson Junction

Bob de Ronde¹, Chuan Li¹, Yingkai Huang² and Alexander Brinkman^{1,*}



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PHYSICAL REVIEW X 7, 021011 (2017)

Josephson Radiation from Gapless Andreev Bound States in HgTe-Based Topological Junctions



PHYSICAL REVIEW X 7, 021011 (2017)

Josephson Radiation from Gapless Andreev Bound States in HgTe-Based Topological Junctions



ARTICLE

https://doi.org/10.1038/s41467-018-08161-2

OPEN

Nature Comm. 10:245 (2019)

Observation of the 4π -periodic Josephson effect in indium arsenide nanowires

Dominique Laroche ¹, Daniël Bouman ¹, David J. van Woerkom ¹, Alex Proutski¹, Chaitanya Murthy², Dmitry I. Pikulin³, Chetan Nayak^{2,3}, Ruben J.J. van Gulik¹, Jesper Nygård⁴, Peter Krogstrup⁴, Leo P. Kouwenhoven^{1,5} & Attila Geresdi 1

ARTICLE

https://doi.org/10.1038/s41467-018-08161-2

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Observation of the 4π -periodic Josephson effect in indium arsenide nanowires

OPEN

Dominique Laroche 1, Daniël Bouman 1, David J. van Woerkom 1, Alex Proutski¹, Chaitanya Murthy²,







Our own Results

Device overview

Tunnel junction

Double angle shadow evaporated **AI/AIO_x/AI**



Nanowire junctions

Dirac semimetal: **Cd**₃**As**₂ (collaboration with M. Jung) Semiconductor: **InAs NW**





Multi-dimensional junctions

InAs 2DEG; Topological insulator:HgTe (with D. Weiss' group)Higher-order topological insulator:WTe₂ with 1D hinge states





Measurement setup



Low-ohmic metal film resistor in parallel to the junction to provide a stable voltage drop and to tune the junction into the overdamped regime.

Inspired by Deacon et al., PRX 7, 021011 (2017)

Tunnel junction SQUID (AI-Al₂O₃-AI)



On-chip flux line allows tuning the

supercurrent through the dc SQUID



PhD thesis of Roy Haller

Tunnel junction SIS: Shapiro steps



 $f_{in} = 2.5 \ GHz$. Note, the missing first odd step! V measurements by **Dario Sufra** et al. (master student **2018-19**)

 $V_l = l \cdot h f_{in}/2e$

master thesis of Dario Sufra and PhD thesis of Roy Haller

Tunnel junction SIS: Josephson radiation



$$V = rac{h}{2e} f_{
m det} \ ... V = rac{h}{2e} f_{
m det} \ ... V = rac{h}{2e} (f_{
m det} + f_{
m env}) \ ... V = rac{h}{2e} (f_{
m det} + 2f_{
m env}) \ ... V = rac{h}{e} f_{
m det}$$

expected 2e-peak position down-converted emission peak position of a 4π-signal

- No features of higher-order tunneling events due to low junction transparency
- No evidence of the 4π signal
- Down-conversion of the AC Josephson signal to lower energy



The energy 2eV is delivered to **two photons**, one that enters a cavity mode (environmental mode, which could be the plasma mode), the other the detector.

Nanowire JJ junction: Cd₃As₂ (Dirac S



Material platform:

- Dirac semimetal
- Ultrahigh carrier mobility
- Nontrivial surface states

A.Q. Wang et al., PRL 121, 237701 (2018)



- Evaporated Al leads define the junction
- Top gate structure isolated by a 20 nm thick HfO₂ layer

Anomalous evolution of the critical current as function of gate voltage could stem from surface scattering.

C.Z. Li et al., PRB 97, 115446 (2018)



by Melissa Osterwalder (master student 2019), Roy Haller and in collab. with Minkyung Jung

Nanowire JJ junction: Cd₃As₂ (Dirac SI

Emission at constant detection frequency as function of top gate voltage



Nanowire junction: Cd₃As₂



Nanowire junction: Cd₃As₂



by Melissa Osterwalder (master student 2019), Roy Haller and in collab. with Minkyung Jung

3d HgTe TI – junction (with D. Weiss' group)



Material platform:



- superconducting interacts with ٠ surface states
- possible formation of • Majorana fermions

C. Brüne et al., PRL 106, 126803 (2011)

Weak gate tunability :



3d TI junction: HgTe





Topological 1e-emission not detected

- too high electronic temperature?
- bulk-contribution too large ?
- lack of sensitivity?

Environmental modes are suppressed at elevated temperatures and applied in-plane magnetic field



3d TI junction: HgTe



3d TI junction: HgTe



by Roy Haller (unpublished)

 $f_{pump} = 2 GHz$ ls on!

Conclusion 1. Part

- We have studied both the **AC Josephson emission** and **Shapiro steps** mostly in the **overdamped limit of Josephson junctions** made from: Al-Al-oxide, InAs nanowires, a Dirac semimetal and HgTe 3d topological insulator a WTe₂ Weyl semimetal (or higher-order topological material) and InAs quantum well material..
- While first odd Shapiro step can be missing (also in trivial junctions), it reappears at high enough microwave input frequency!
- The "fractional" AC emission at frequency $f_{topo} = eV/h$ has not been observed, in none of the samples (until now)!
- **Reasons (?):** overheating leading to parity flipping; too large trivial "bulk" current and a not high enough sensitivity to detect the 4π signal
- What can we do? Design the RF part such that Josephson emission can be carried away "fully". Need a 10Ω transmission line that smoothly evolves into a 50Ω



End Lecture I